

TOSHIBA

2SJ338

TOSHIBA FIELD EFFECT TRANSISTOR SILICON P CHANNEL MOS TYPE

2SJ338

AUDIO FREQUENCY POWER AMPLIFIER APPLICATION

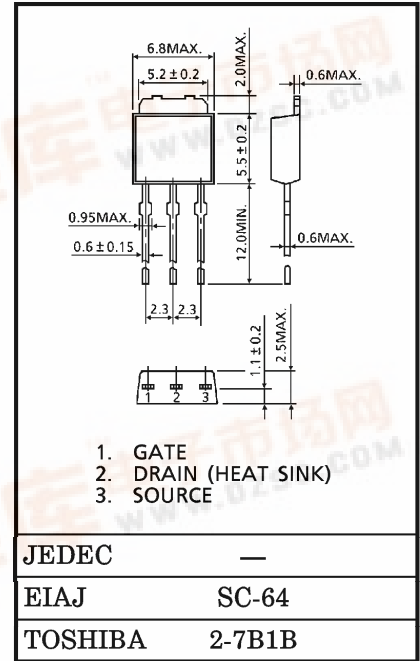
INDUSTRIAL APPLICATIONS

Unit in mm

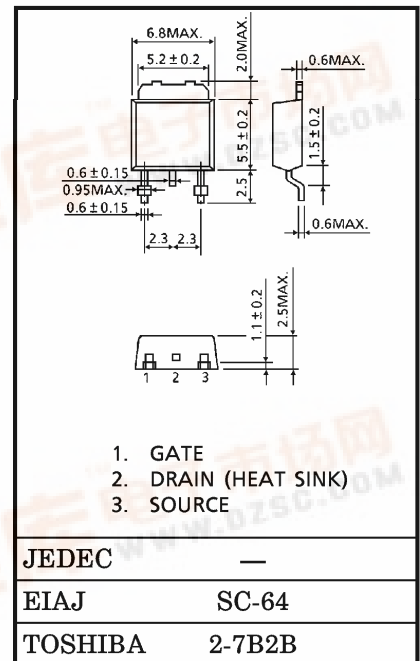
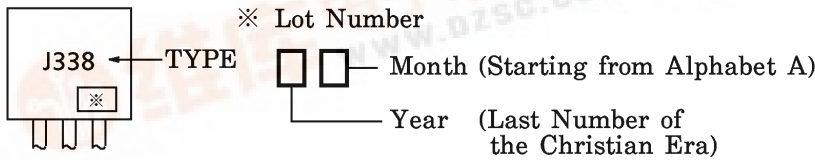
- High Breakdown Voltage : $V_{DSS} = -180V$
- High Forward Transfer Admittance : $|Y_{fs}| = 0.7S$ (Typ.)
- Complementary to 2SK2162

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	-180	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	I_D	-1	A
Power Dissipation ($T_c = 25^\circ C$)	P_D	20	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$



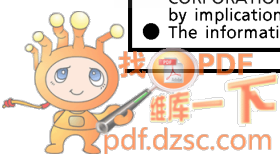
MARKING



Weight : 0.36g

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GSS}	$V_{DS}=0, V_{GS}=\pm 20V$	—	—	± 100	nA
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -10mA, V_{GS}=0$	-180	—	—	V
Gate -Source Cut-off Current	$V_{GS(OFF)}$ (Note)	$V_{DS} = -10V, I_D = -10mA$	-0.8	—	-2.8	V
Drain-Source Saturation Voltage	$V_{DS(ON)}$	$I_D = -0.6A, V_{GS} = -10V$	—	-1.2	-3.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -0.3A$	—	0.7	—	S
Input Capacitance	C_{iss}	$V_{DS} = -10V, V_{GS}=0, f=1MHz$	—	210	—	pF
Output Capacitance	C_{oss}	$V_{DS} = -10V, V_{GS}=0, f=1MHz$	—	90	—	pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -10V, V_{GS}=0, f=1MHz$	—	45	—	pF

(Note) $V_{GS(OFF)}$ Classification O : $-0.8 \sim -1.6$, Y : $-1.4 \sim -2.8$

**This transistor is the electrostatic sensitive device.
Please handle with caution.**